



Semester Project in TESYS, 2023

## Front-To-Back Implementation of a 3-Bit Analog to Digital Converter in XFAB 0.35 $\mu$ m CMOS Technology

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*Elias Biehl*

Supervisor: Prof. Dr.-Ing. Andreas König

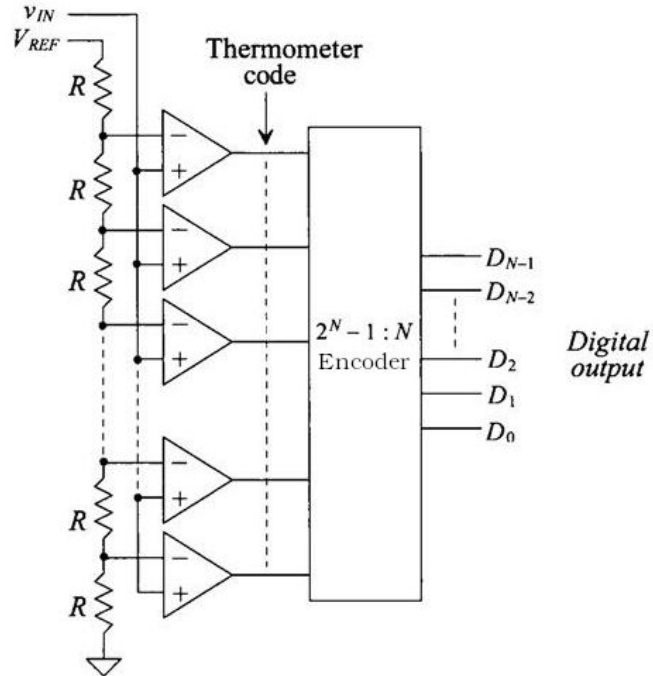


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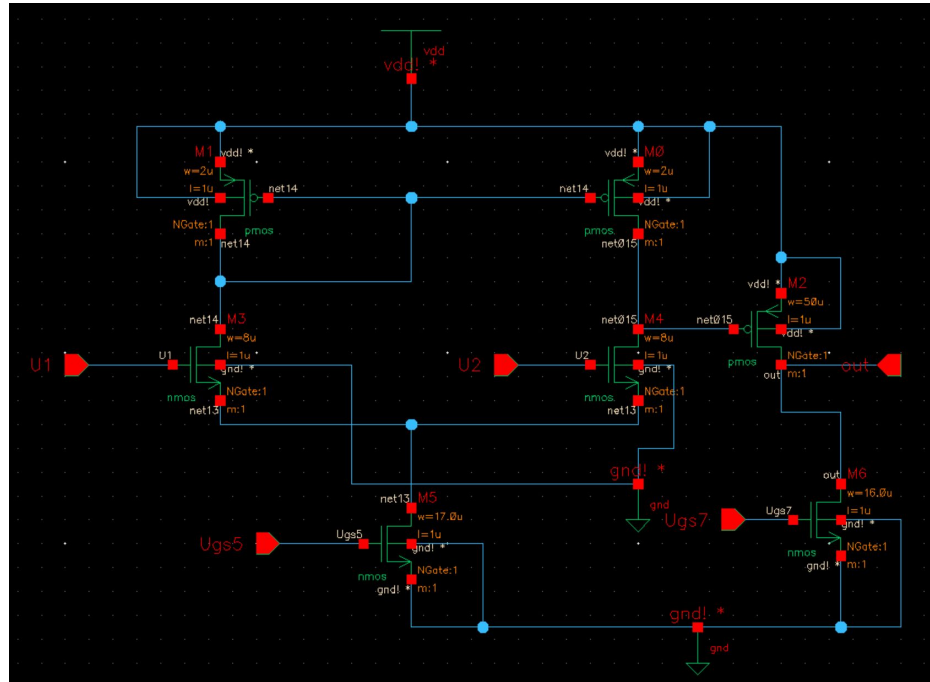
## Parts of the project



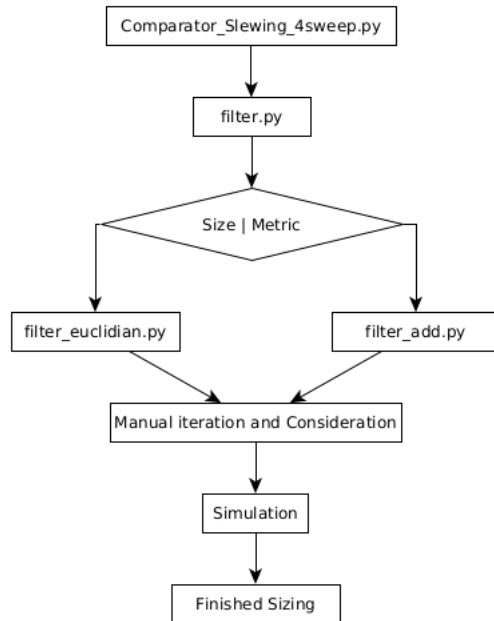
- 8 matched Resistors
- Thermometer Code Encoder
- 7 Comparators
- all Resistors have the same size due to simplification ( $R=4124.4 \text{ Ohm}$ )

## NMOS Comparator Schematic

- Design after Allen/Holberg (7 transistor design)
  - a. Design flow on next slide
- Prioritize in order:
  - a. Wide CMR-range
  - b. Size
  - c. Speed
  - d. Allowed tolerance (CI)

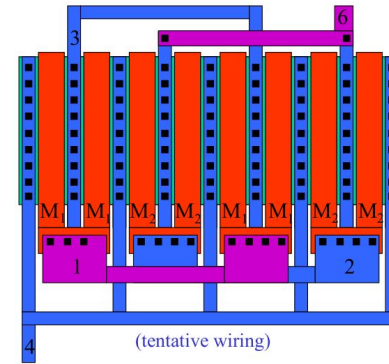
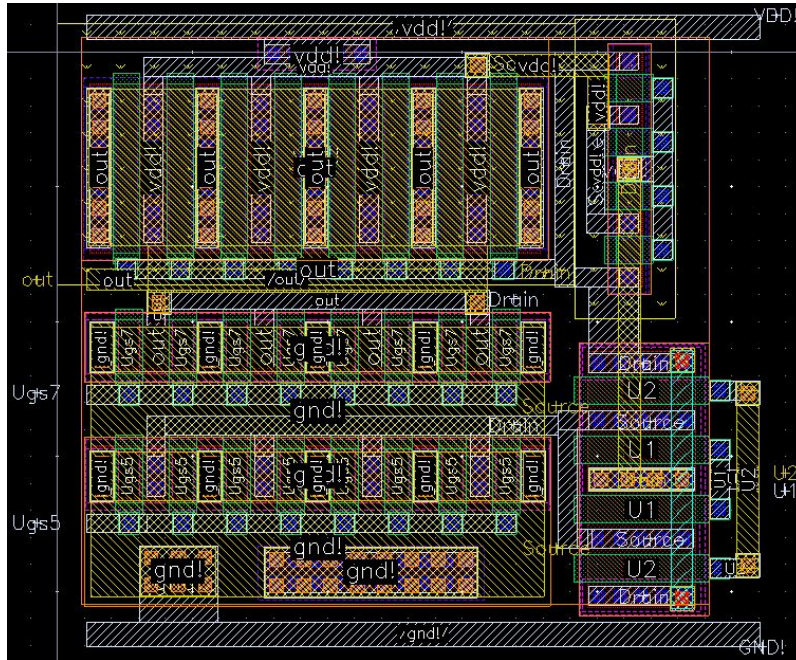


## NMOS Comparator Schematic



- `Comparator_Slewing_4sweep.py`:
  - 4-dimensional parameter sweep
- `filter.py`:
  - exclude corner sizes ( $100\mu\text{m}$  &  $1\mu\text{m}$ )
- `filter_euclidian.py`:
  - select everything below certain top boundaries e.g. for  $P_{\text{diss}}$  or aspect ratios
- `filter_add.py`:
  - Include all solutions with a CMR greater than a given value
- Results hold size and Bias-Voltage

# NMOS Comparator Layout



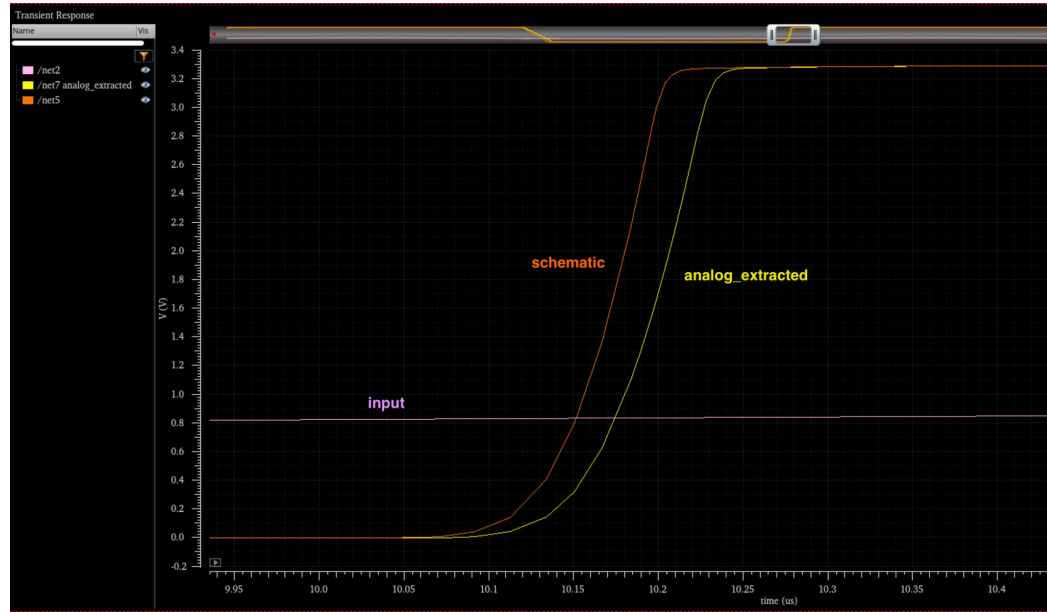
- Interdigitized “folded/matched” Transistors
- Allows matched positioning & sizing
- $23.4\mu\text{m} \times 25.1\mu\text{m}$



## NMOS Comparator

Analog extracted

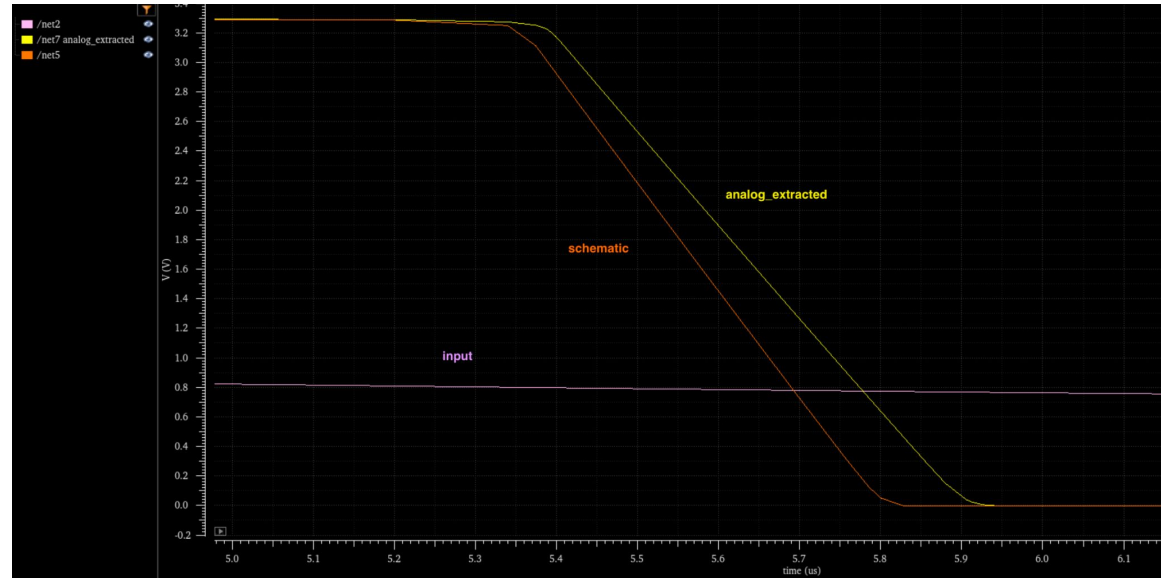
- Slightly bigger capacitance in layout resulting in slower speed
- Input Sine, 100kHz, 825mV, amp 100mV



## NMOS Comparator

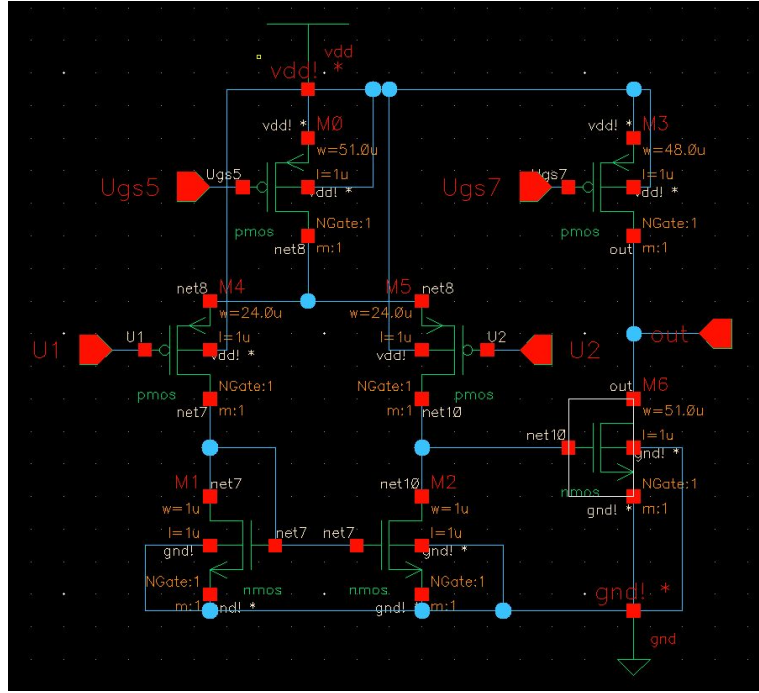
Analog extracted

- Slightly bigger capacitance in layout resulting in slower speed
- Input Sine, 100kHz, 825mV, amp 100mV





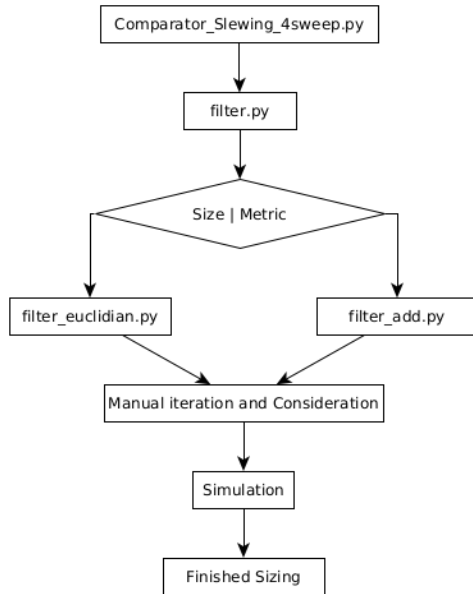
# PMOS Comparator Schematic



- Design after Allen/Holberg (7 transistor design)
  - a. Design flow on next slide
- Prioritize in order:
  - a. Wide CMR-range
  - b. Size
  - c. Speed
  - d. Allowed tolerance (CI)

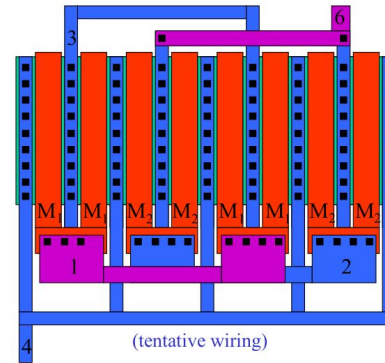
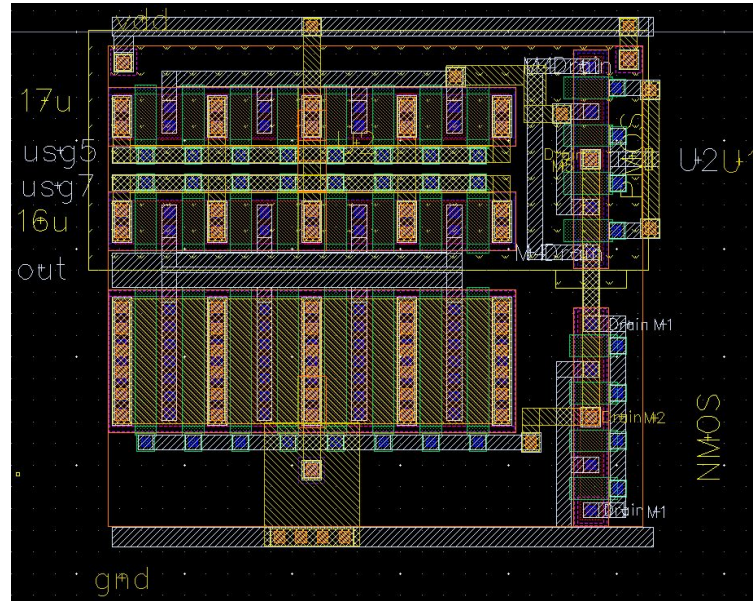


## PMOS Comparator Schematic



- `Comparator_Slewing_4sweep_P MOS.py`:
  - 4-dimensional parameter sweep
- `filter.py`:
  - exclude corner sizes (100 $\mu$ m & 1 $\mu$ m)
- `filter_euclidian.py`:
  - select everything below certain top boundaries e.g. for  $P_{diss}$  or aspect ratios
- `filter_add.py`:
  - Include all solutions with a CMR greater than a given value
- Results hold size
- Bias-Voltage needed to be extracted experimentally

# PMOS Comparator Layout

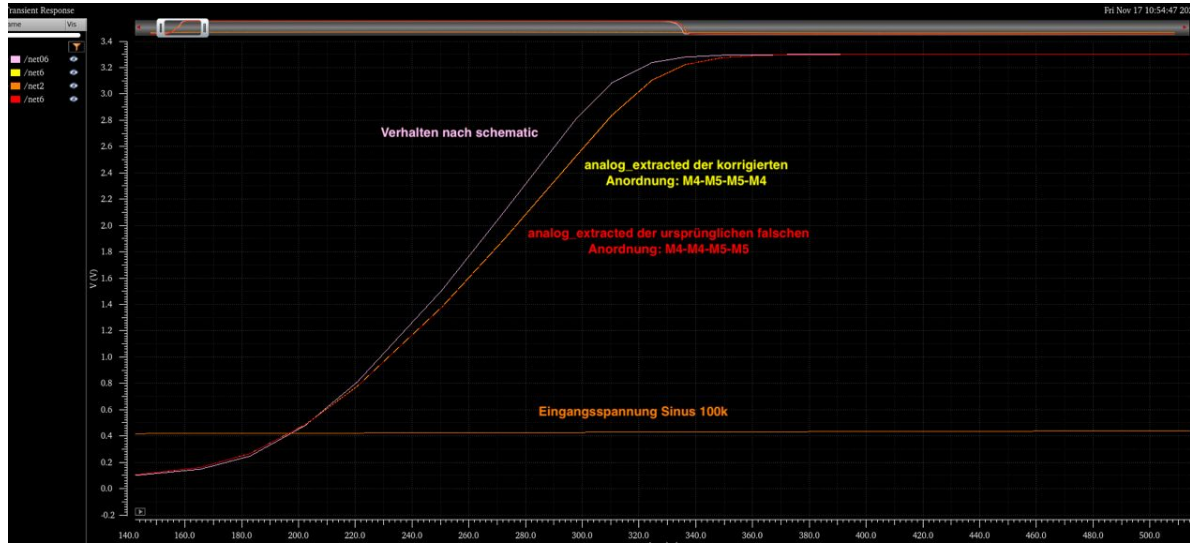


- Interdigitated "folded/matched" Transistors
- Allows matched positioning & sizing
- 24.475 $\mu\text{m}$  x 25.525 $\mu\text{m}$



# PMOS Comparator

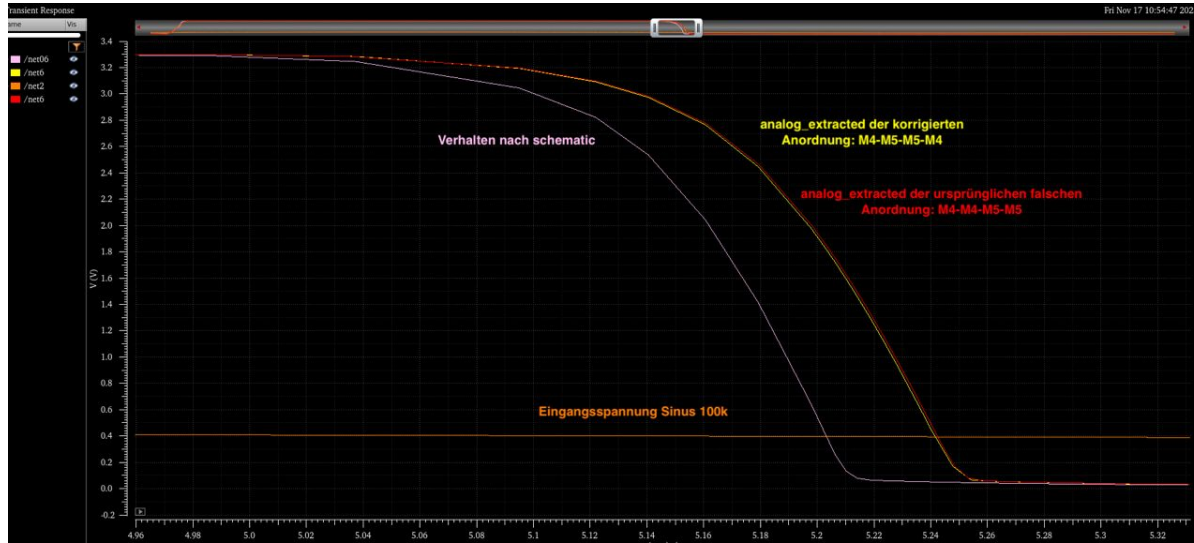
Analog extracted - RE & FE



- Slightly bigger capacitance in layout resulting in slower speed
- simulation with Sine, 100kHz, offset: 412.5mV, amp: 100mV

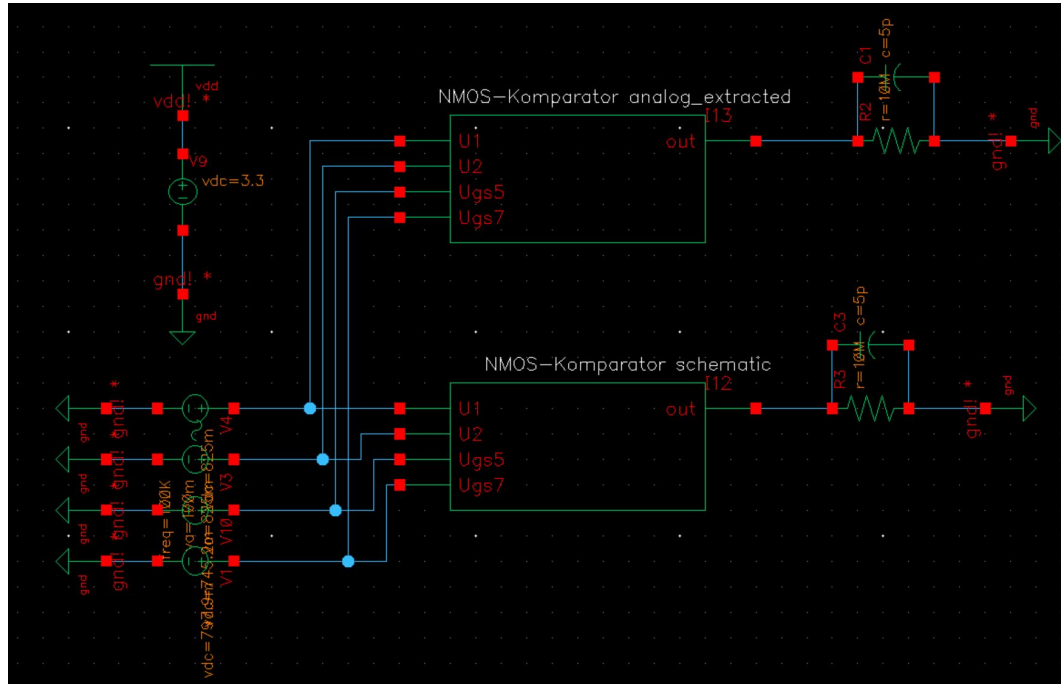
# PMOS Comparator

Analog extracted - RE & FE



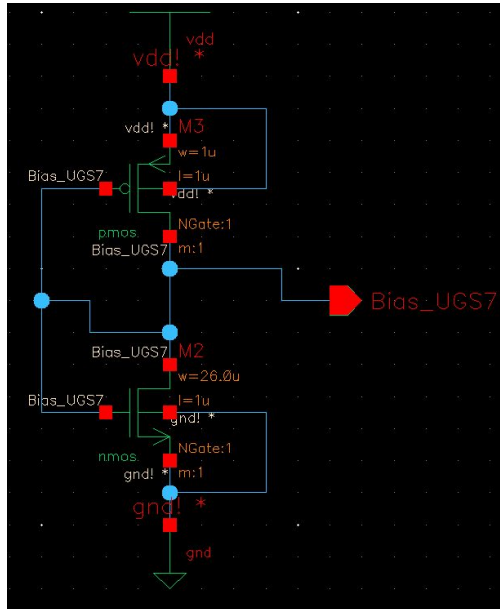
- Slightly bigger capacitance in layout resulting in slower speed
- simulation with Sine, 100kHz, offset: 412.5mV, amp: 100mV

# PMOS / NMOS Comparator Testbench



## BIAS Circuit for NMOS Comparator

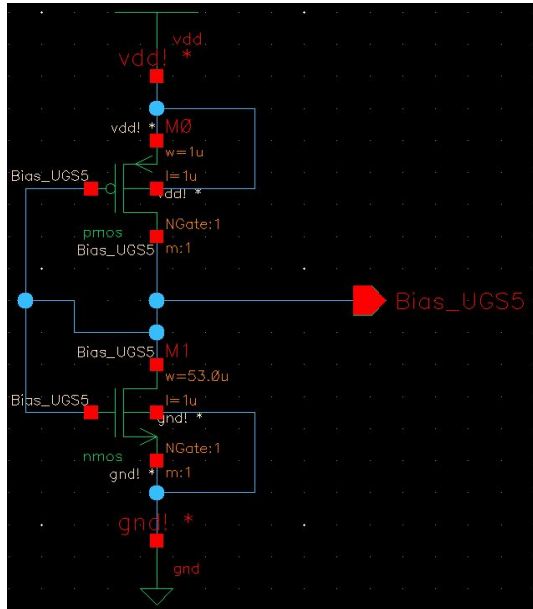
### Schematic



- Simple voltage divider per MOST-Diode with near round transistor sizes
  - result with smallest rounding error used
- Analytical design for given wanted voltage
  - Slides 5-25/26
  - per simple python calculation scripts:
    - Bias-Circuit-PMOS-sweep\_usg5.py
    - Bias-Circuit-PMOS-sweep\_usg7.py
  - Sweep current through circuit
  - Current/Area tradeoff

# BIAS Circuit for NMOS Comparator

## Schematic

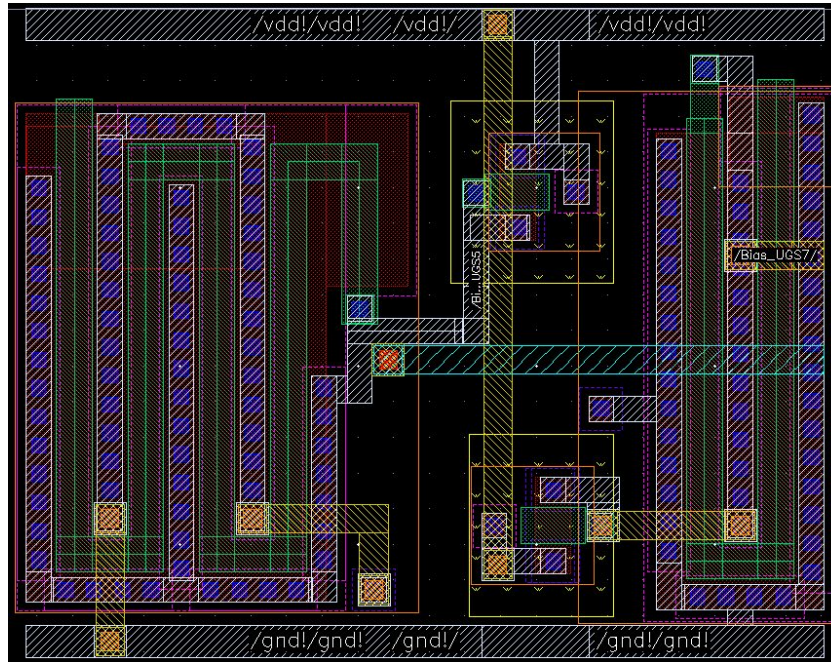


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# BIAS Circuit for NMOS Comparator

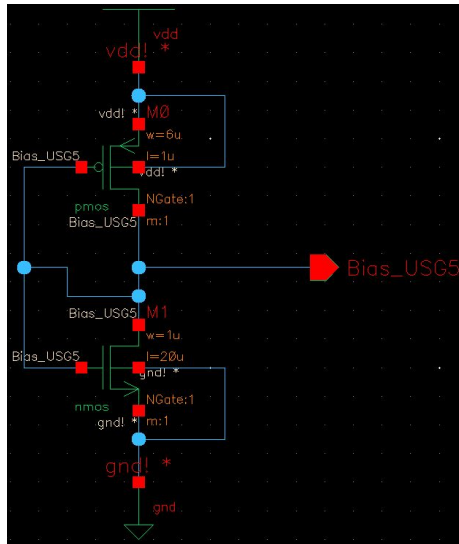
## Layout



- Lengths not easy matchable (need to go through DRC & LVS) for very long
- Meanderized transistors to save space for very long transistors
- Both bias circuits into one layout (size matching in layout needed)
- $18.2\mu\text{m} \times 23.075\mu\text{m}$

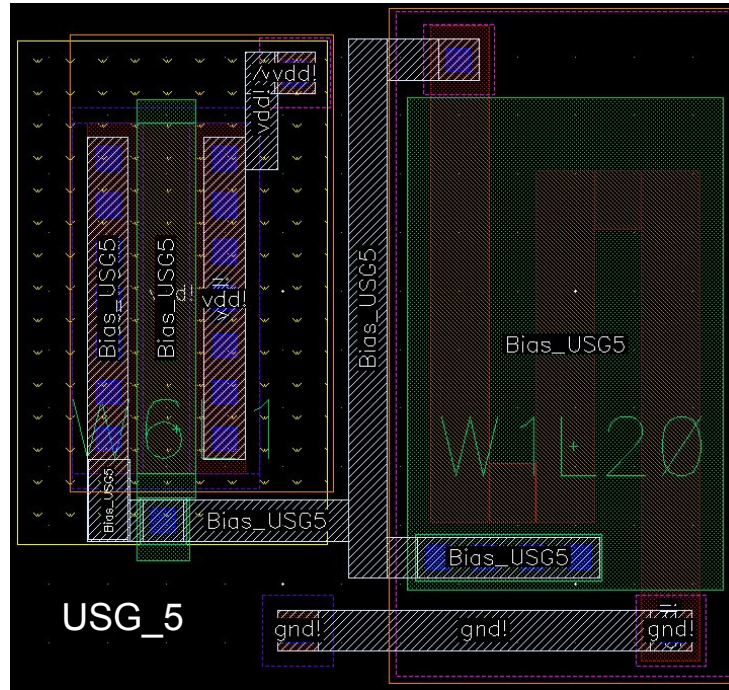
## BIAS Circuit for PMOS Comparator

### Schematic



- Simple voltage divider per MOST-Diode with near round transistor sizes
  - result with smallest rounding error used
- Analytical design for given wanted voltage
  - Slides 5-25/26
  - per simple python calculation scripts
  - Sweep current through circuit
  - Current/Area tradeoff
- No combined layout was easy to implement

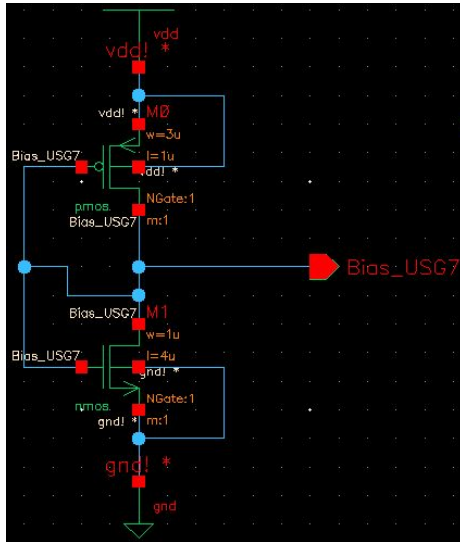
## BIAS Circuit ( $U_{SG5}$ ) for PMOS Comparator Layout



- Lengths not easy matchable (need to go through DRC & LVS) for ultra long
- meanderized transistors to save space for very long transistors
- Both bias circuits into one layout (size matching in layout needed)
- $12.25\mu\text{m} \times 11.525\mu\text{m}$  (first)
- $14.5\mu\text{m} \times 6.15\mu\text{m}$  (second)

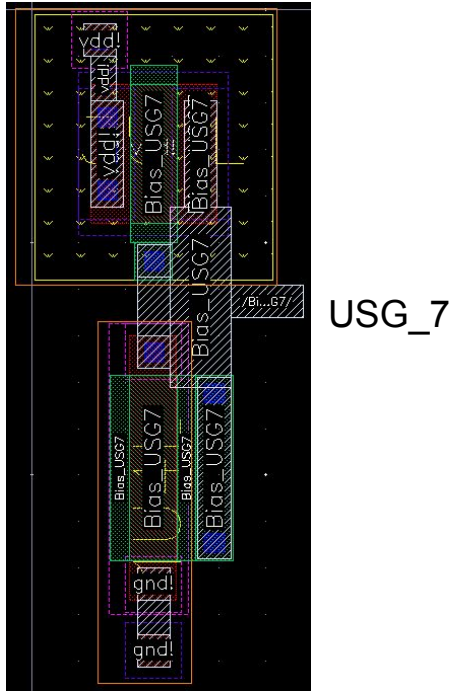
# BIAS Circuit for PMOS Comparators

## Schematic



- Simple voltage divider per MOST-Diode with near round transistor sizes
  - result with smallest rounding error used
- Analytical design for given wanted voltage
  - Slides 5-25/26
  - per simple python calculation scripts
  - Sweep current through circuit
  - Current/Area tradeoff
- No combined layout was easy to implement

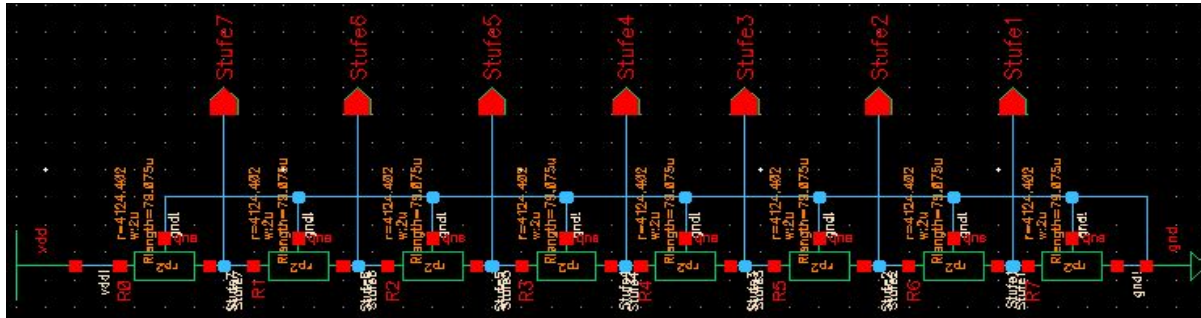
## BIAS Circuit ( $U_{SG7}$ ) for PMOS Comparator Layout



- Lengths not easy matchable (need to go through DRC & LVS) for ultra long
- Both bias circuits into one layout (size matching in layout needed)
- $12.25\mu\text{m} \times 11.525\mu\text{m}$  (first)
- $14.5\mu\text{m} \times 6.15\mu\text{m}$  (second)

## Resistor Chain Schematic

- Current limit set to  $100\mu\text{A}$
- For Supply voltage of  $3.3\text{V}$ :
  - $3.3\text{V} / 100\mu\text{A} = 33.3\text{k}\Omega$
- Used High-Res Poly2 Instances from PrimLib
- due to simplification: all resistors have the same value
- Same step size across full range -> goal was to simplify layout design (homogenous structure)



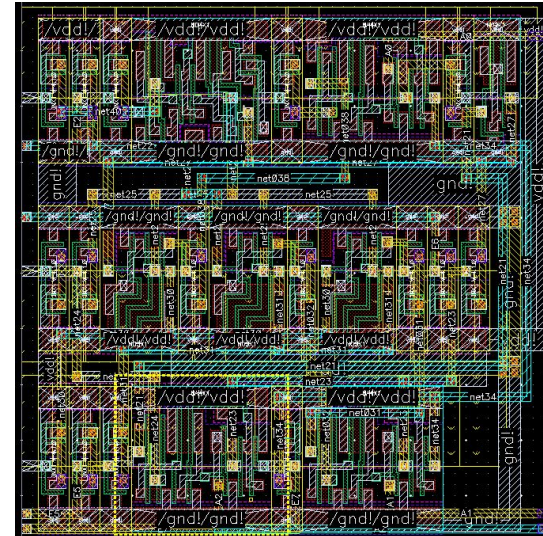
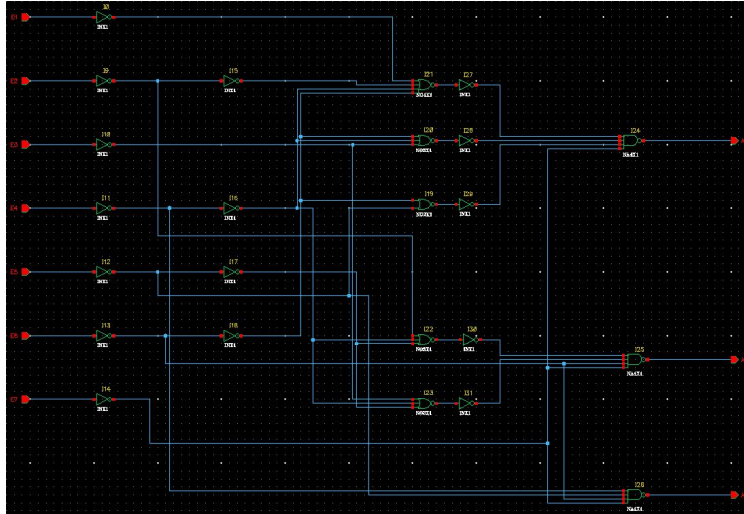
## Resistor Chain Layout



- Layout generated from cells of PrimLib
- Connection of strips via MET1
- Contacting through MET1



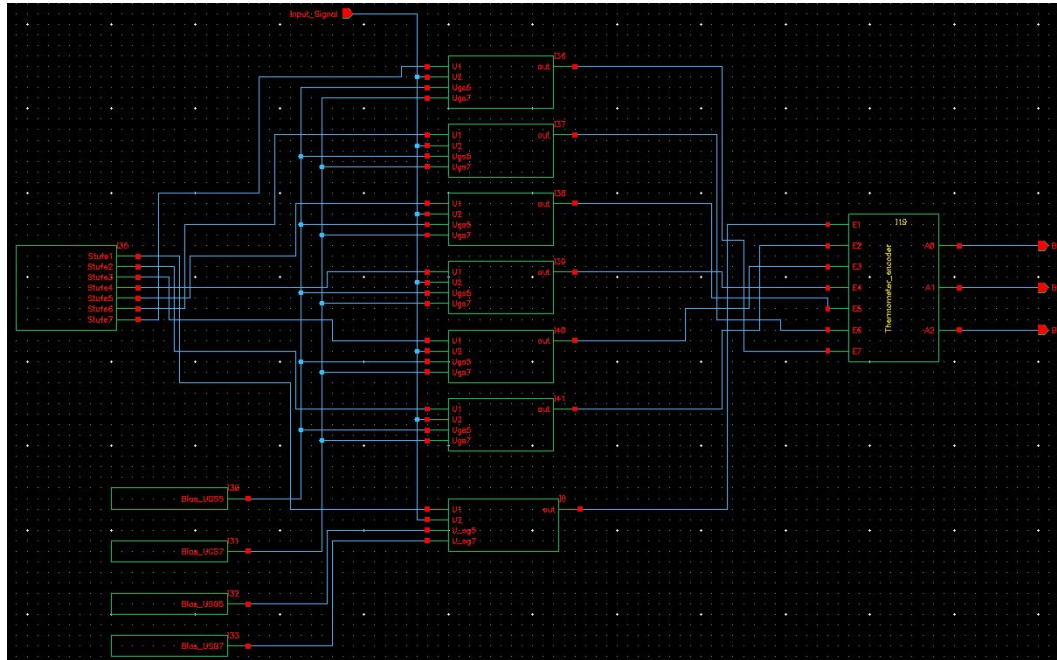
## Encoder



- Schematic & Layout provided from Lukas Birkenmeier for MeLLab



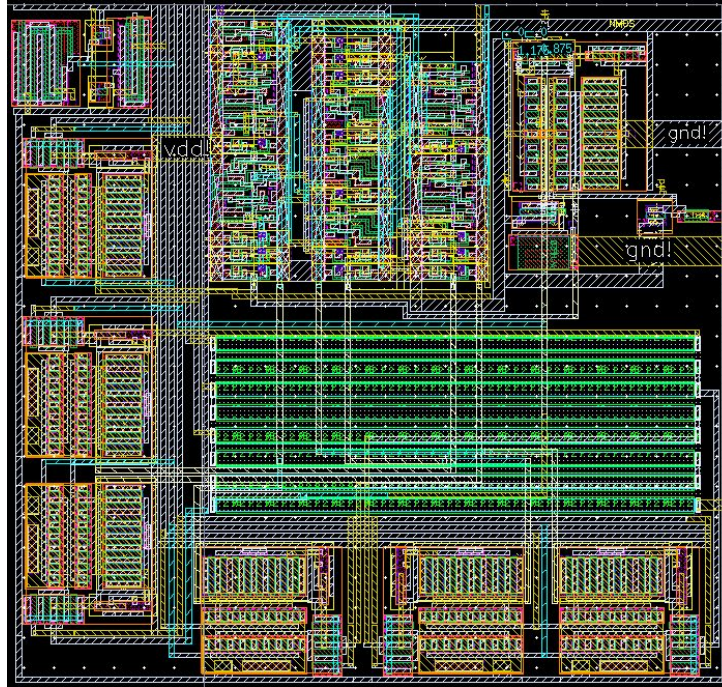
## Top level design & wiring Schematic



- 4 Bias Cells
- Resistor Chain (8)
- Encoder
- 7 Comparators

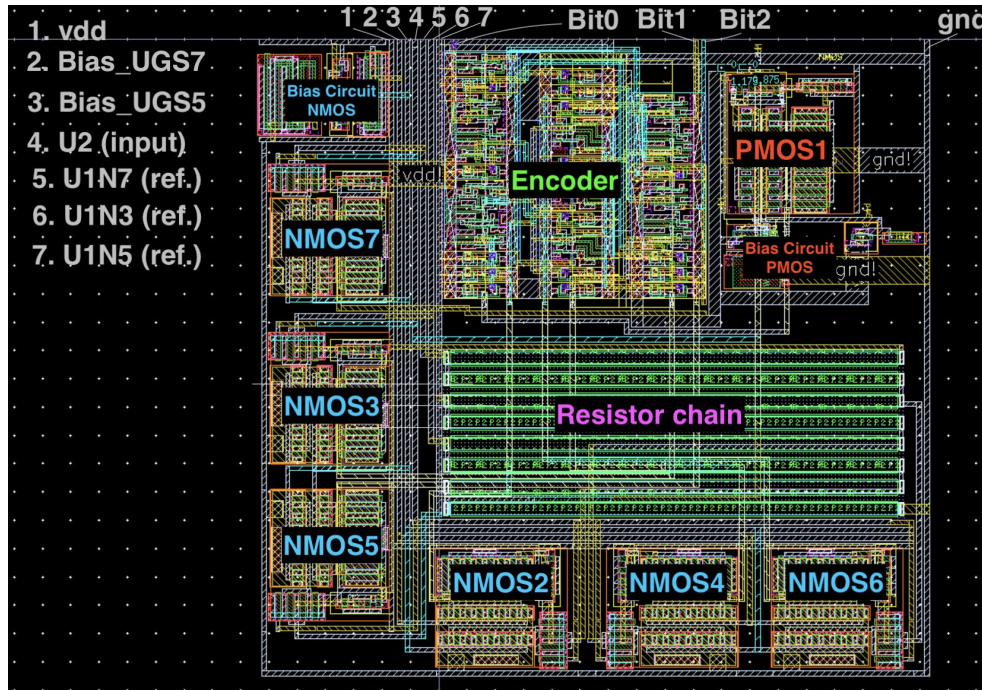
## Top level design & wiring

### Layout



- Main Voltage “Bus” to distribute voltages
- Floorplan pre-planned in painting software
- Minimal Area and 1:1 Aspect Ratio prioritised
- Mirrored positioning of Comparators for less area
  - esp. for Bias-voltage distribution
- 112.475 $\mu\text{m}$  x 118 $\mu\text{m}$

## Top level design & wiring Layout



U1N7, U1N3, U1N5  
not input/outputs,  
just internal  
connections that  
can be accessed

1. vdd

2. Bias\_UGS7

3. Bias\_UGS5

4. U2 (input)

5. U1N7 (ref.)

6. U1N3 (ref.)

7. U1N5 (ref.)

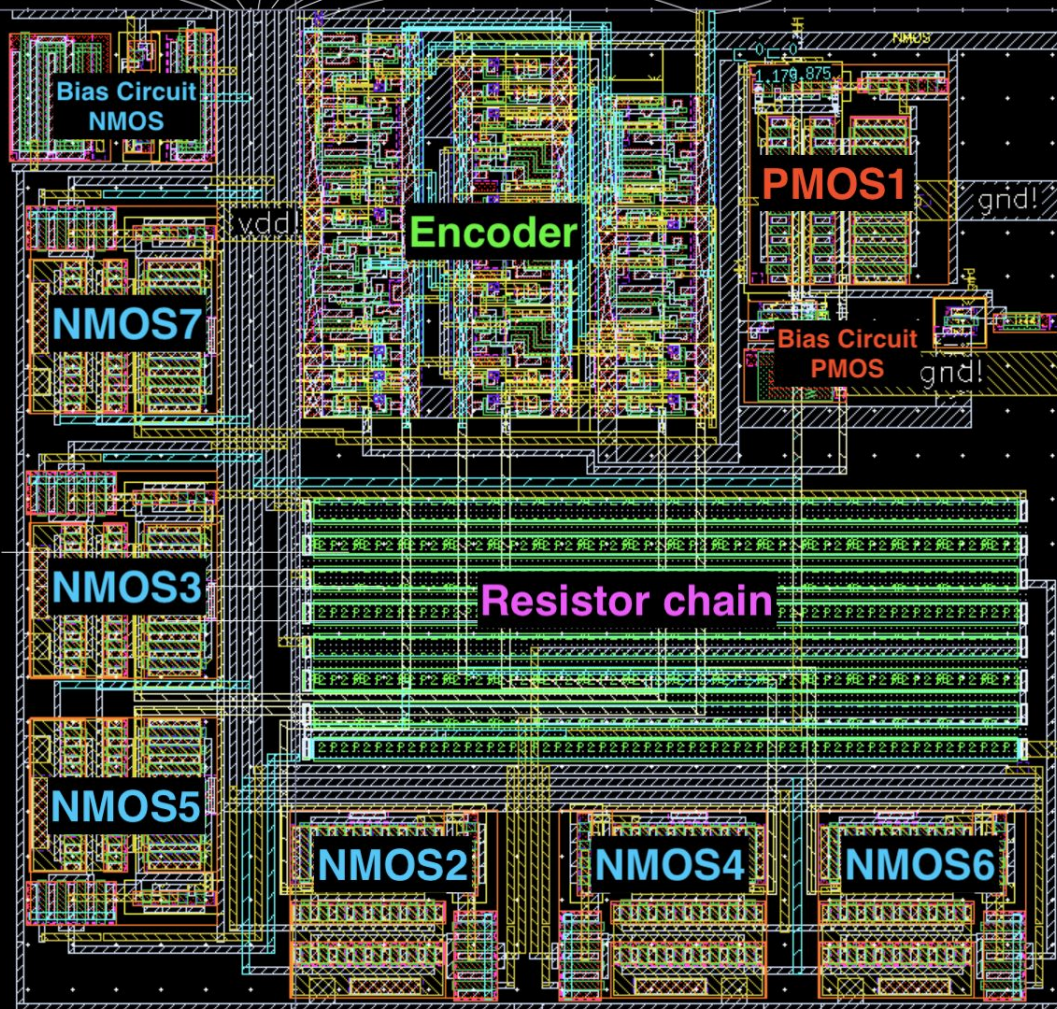
1 2 3 4 5 6 7

Bit0

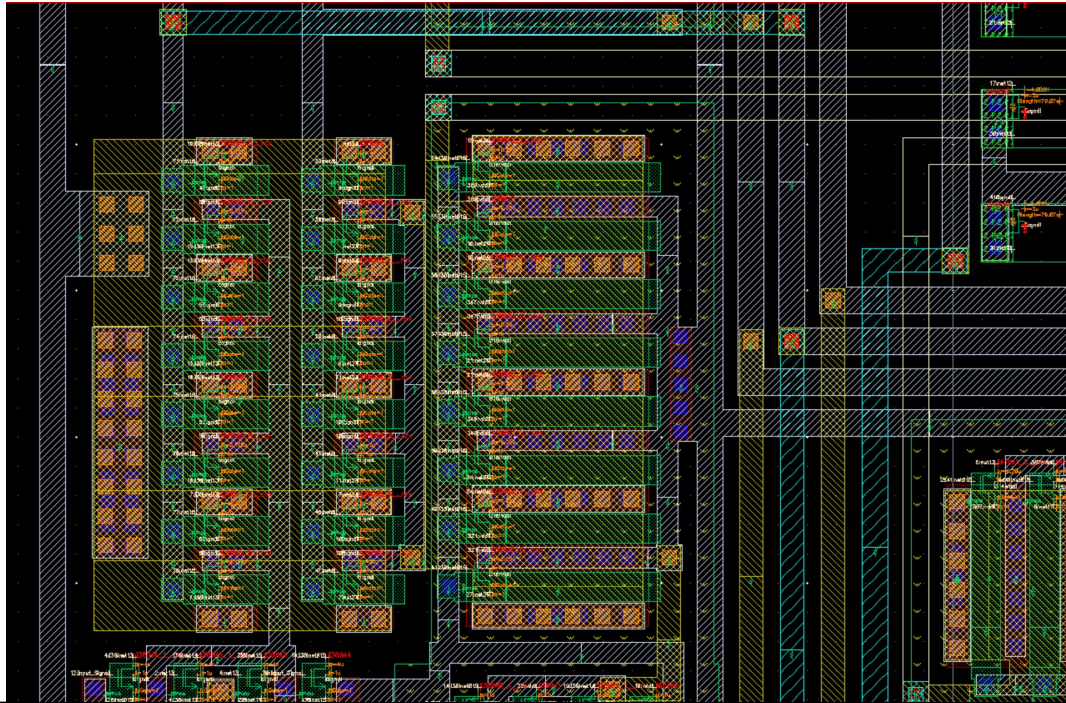
Bit1

Bit2

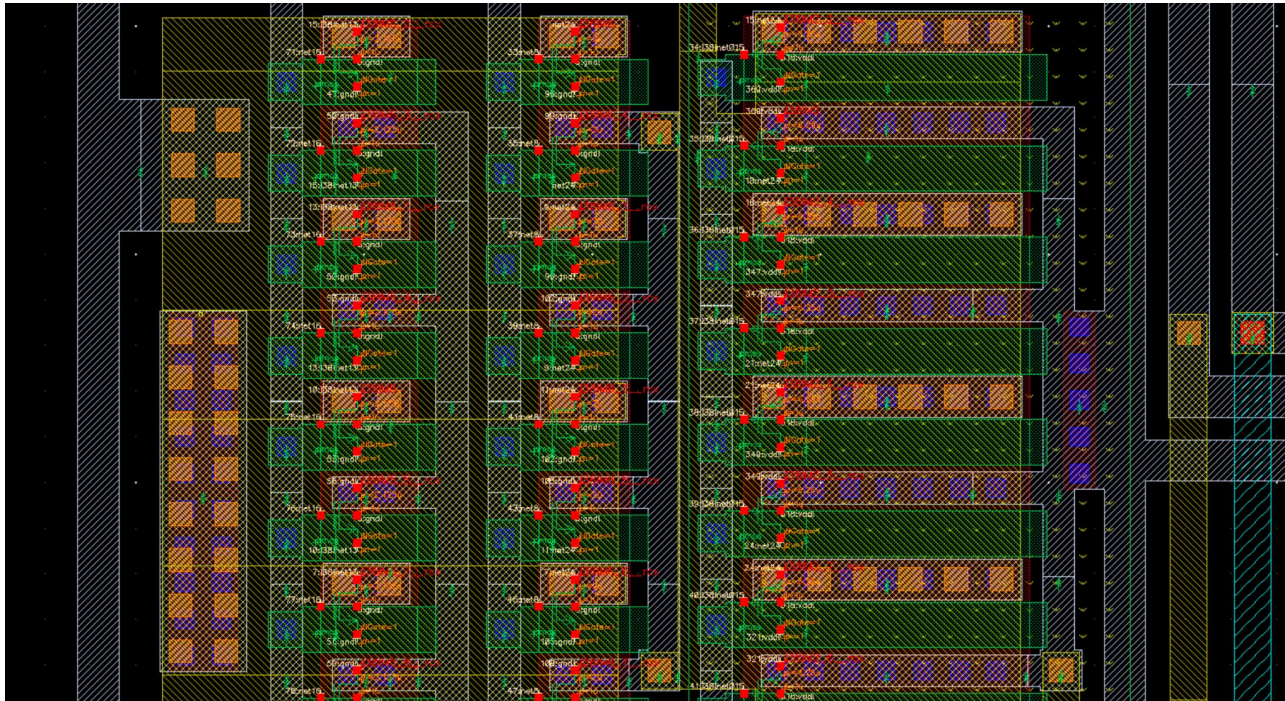
gnd



# Analog extracted, DRC and LVS Layout

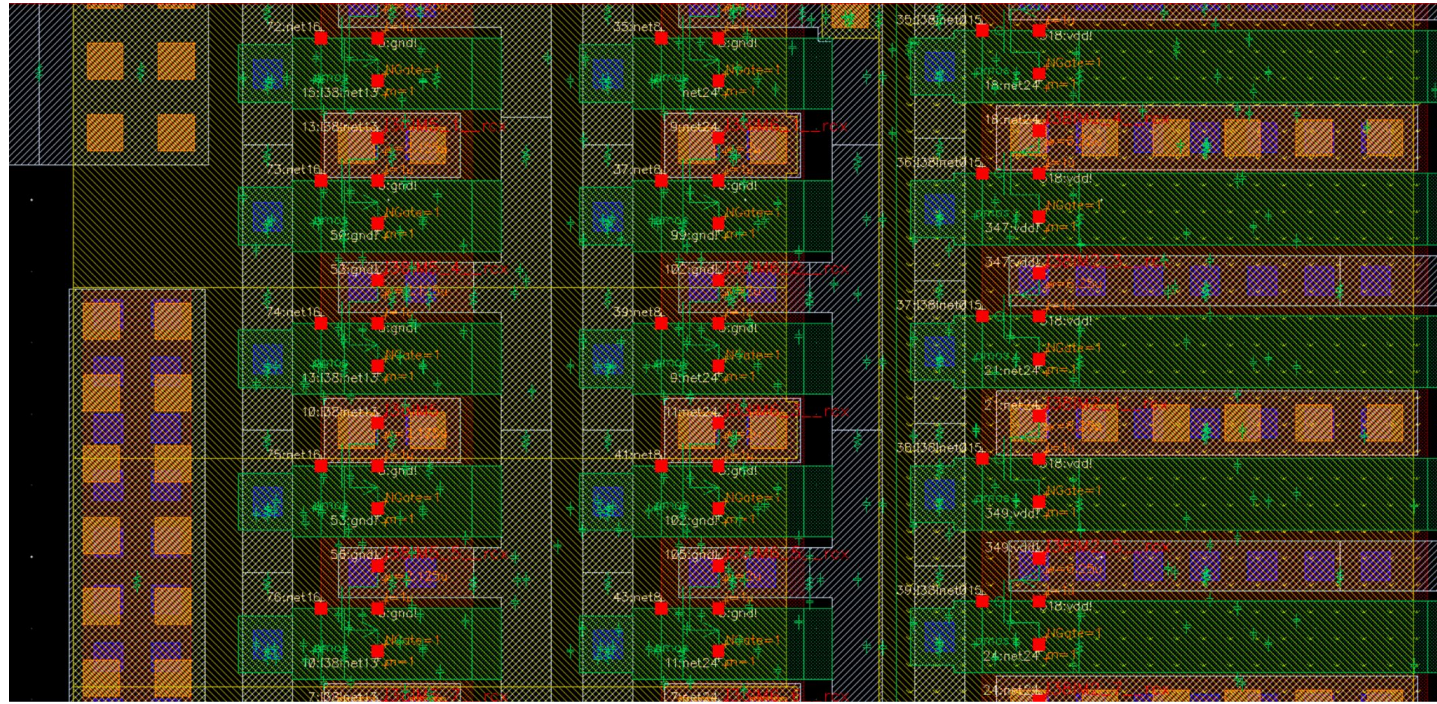


# Analog extracted, DRC and LVS Layout

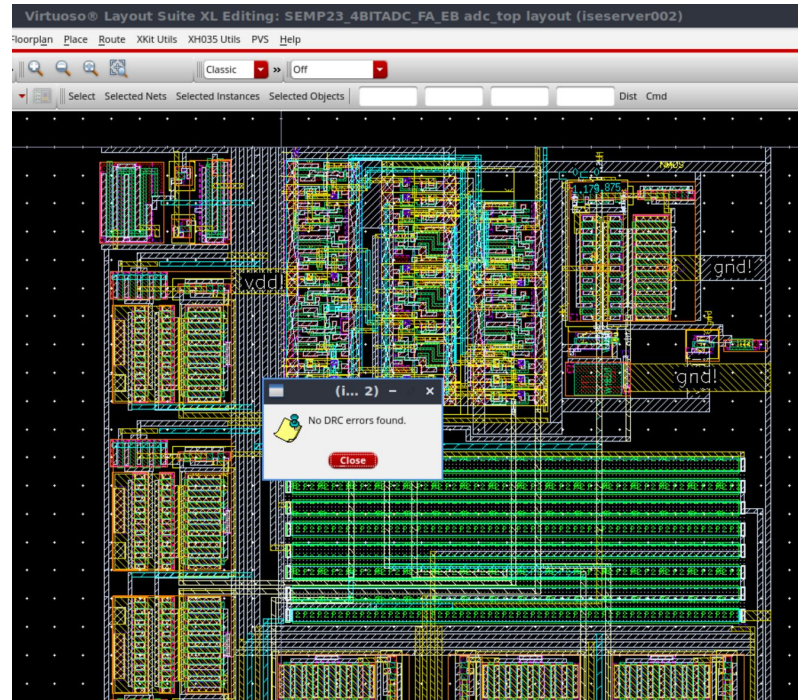


# Analog extracted, DRC and LVS

## Layout

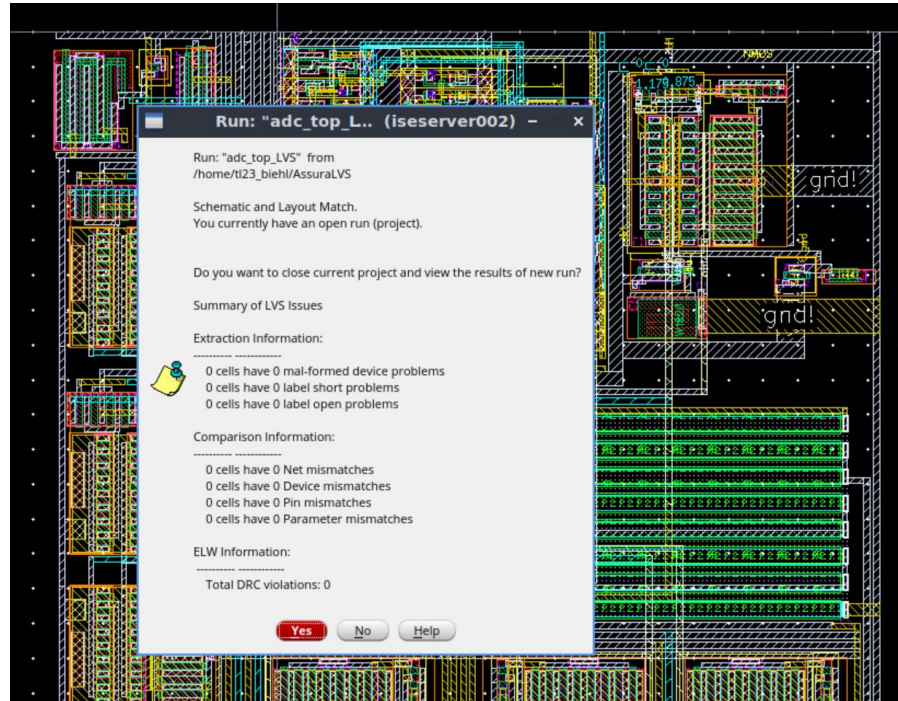


# Analog extracted, DRC and LVS Layout

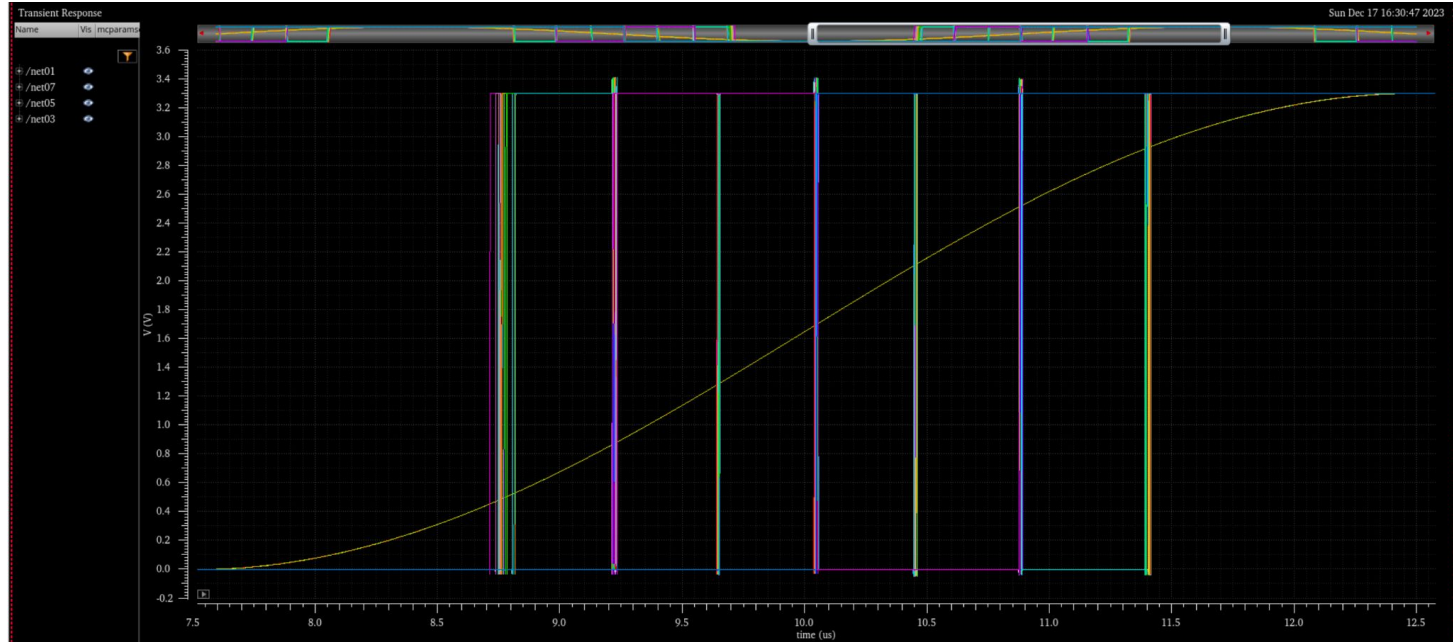




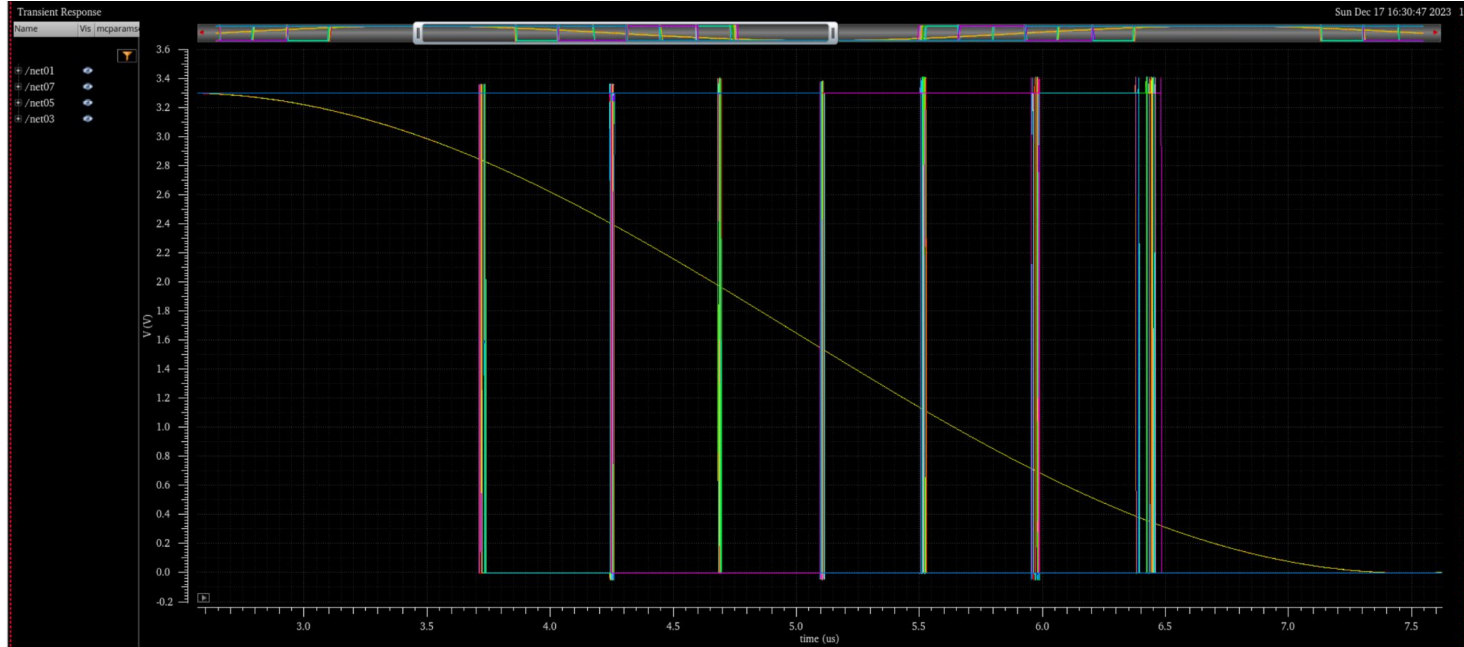
# Analog extracted, DRC and LVS Layout



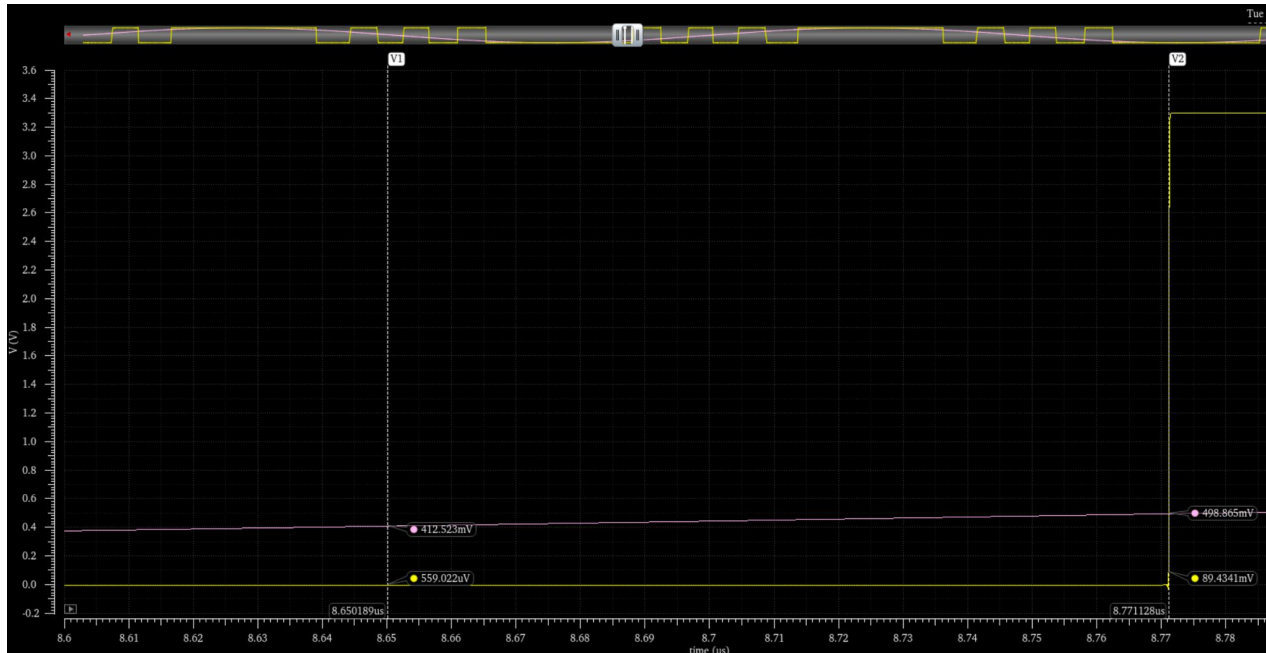
## Monte Carlo (Rising Edge)



## Monte Carlo (Falling Edge)



## Conclusion



- Theoretical/Simulated max. Sample Rate: 8.3MS/s



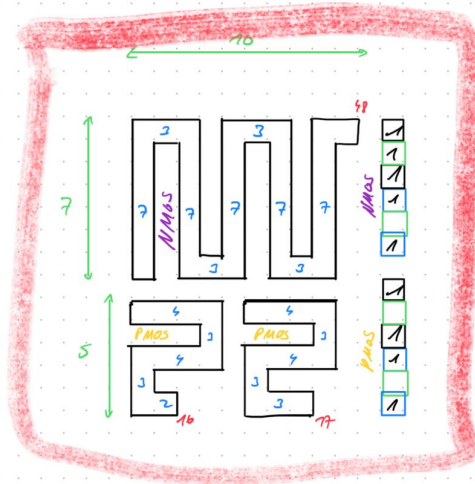
## Conclusion

- Slightly slower and wider spread vs. schematic
- Better Matching & Layout possible
  - especially PMOS comparator
  - also NMOS2 comparator
- Static Power: 1.41735 mW
- Total area:  $1.327 \cdot 10^{-8} \text{ m}^2 = 0.01327 \text{ mm}^2$



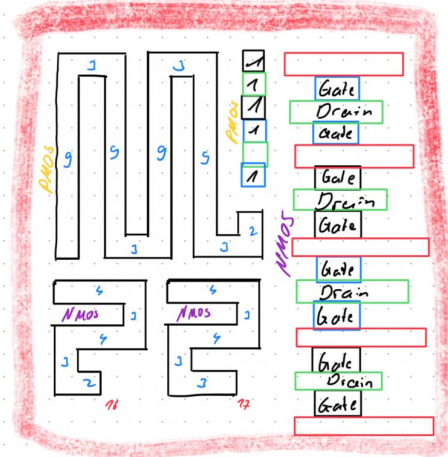
# Planning in Freeform

PMOS layout

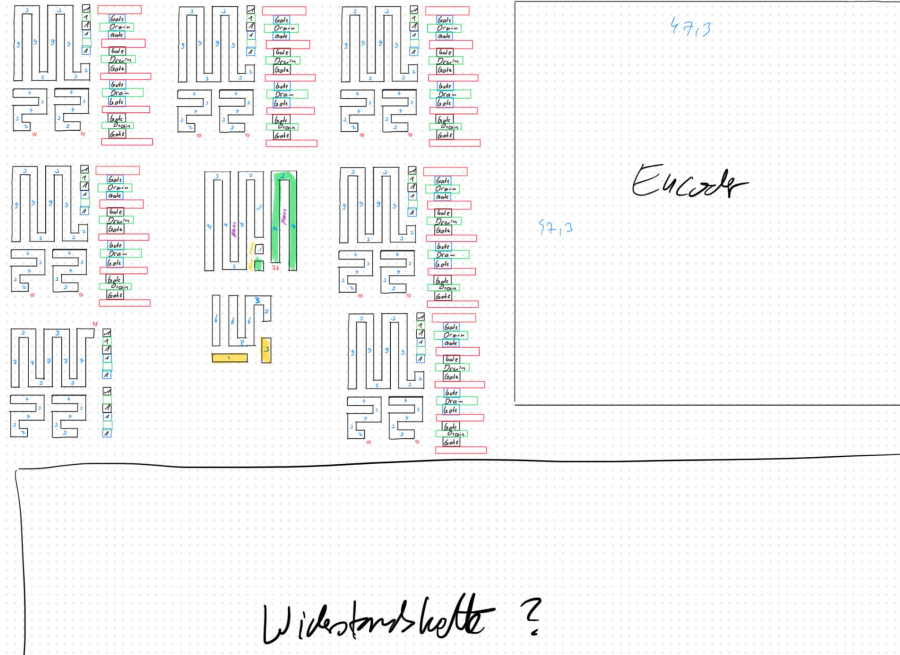


NMOS layout

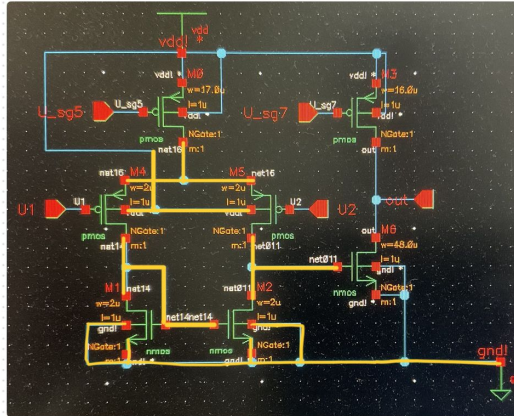
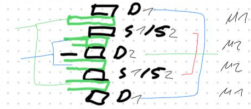
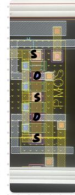
$2 \times 2\mu$      $1 \times 17\mu$      $1 \times 50\mu$   
 $2 \times 8\mu$      $1 \times 16\mu$



# Planning in Freeform



# Planning in Freeform

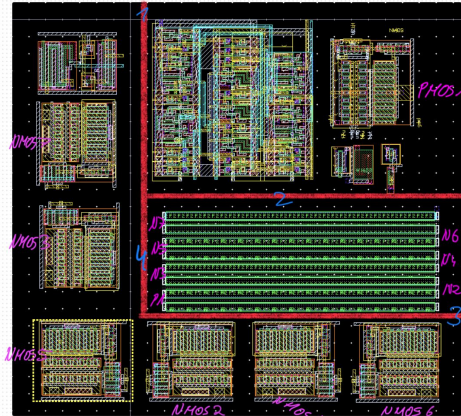


net6 "leicht"  
 net6 only\_2armed  
 net6 14



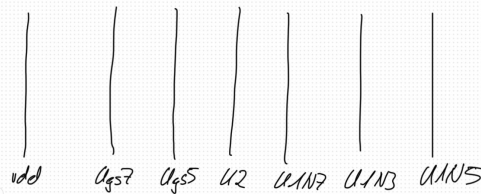


# Planning in Freeform



- Actse 1:
- Bias\_UGS7
  - Bias\_UGS5
  - udl
  - out x 2
  - U1, U2
- Actse 2:
- U2
  - U1 x 5
  - Bias\_UGS7
  - Bias\_UGS5
  - Out 5x
- Actse 3:
- Out 7x
  - U2
  - U1 x 2
- Actse 3:
- Out 3x
  - U2
  - Bias\_UGS7
  - Bias\_UGS5
  - U1 x 3

Actse 1 Legende:



19 % +





Thank you for your attention!  
Questions?



## Sources

- [https://www.researchgate.net/figure/Example-of-a-3-bit-Flash-ADC-4\\_fig15\\_304346665](https://www.researchgate.net/figure/Example-of-a-3-bit-Flash-ADC-4_fig15_304346665)
- TESIS script
- Electronics I/II script
- XFAB application note
- Microelectronic Lab course (Prof. König)

